

Technical Data

NEON® 60 Essential Specifications		
	SEM	FIB
Resolution	1.1 nm @ 20 kV 2.5 nm @ 1 kV	7 nm @ 30 kV guaranteed, 5 nm achievable
Magnification	20x - 900kx	600x - 500kx
Probe Current	4 pA - 20 nA	1 pA - 50 nA
Acceleration Voltage	0.1 - 30 kV	2 - 30 kV
Emitter	Schottky Field Emitter	Ga liquid metal ion source (LMIS)
Gas Injection System	Up to 5 gases for selective etching, enhanced etching, material deposition, insulator deposition	
Detectors	In-column: In-lens: Chamber: BSD: QMS: STEM: 4QBSE:	N/A High Efficiency annular type (SE) ET type (SE) Optional solid state or scintillator type Optional GEMINI® Multimode BF / DF detector Optional
Options	General purpose airlock / Micromanipulator for sample handling	
Specimen Chamber	520 mm ø, 300 mm height 2 x IR CCD-camera included for sample viewing 8" large integrated airlock 210 x 50 mm	
Specimen Stage	X = 152 mm, Y = 152 mm Z = 43 mm, Z. = 10 mm T = -15 - 65° R = 360° continuous	
Image Acquisition	Resolution: from 512 x 384 to 3072 x 2304 pixel, Processing: Pixel averaging, frame averaging, continuous averaging	
Image Display	Two 19" TFT monitors with image displayed at 1024 x 768 pixel	
System Control	Integrated CrossBeam®/SmartSEM® GUI based on Windows XP® operating system, controlled by mouse, control panel, keyboard and joystick	

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